

BLX13C

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

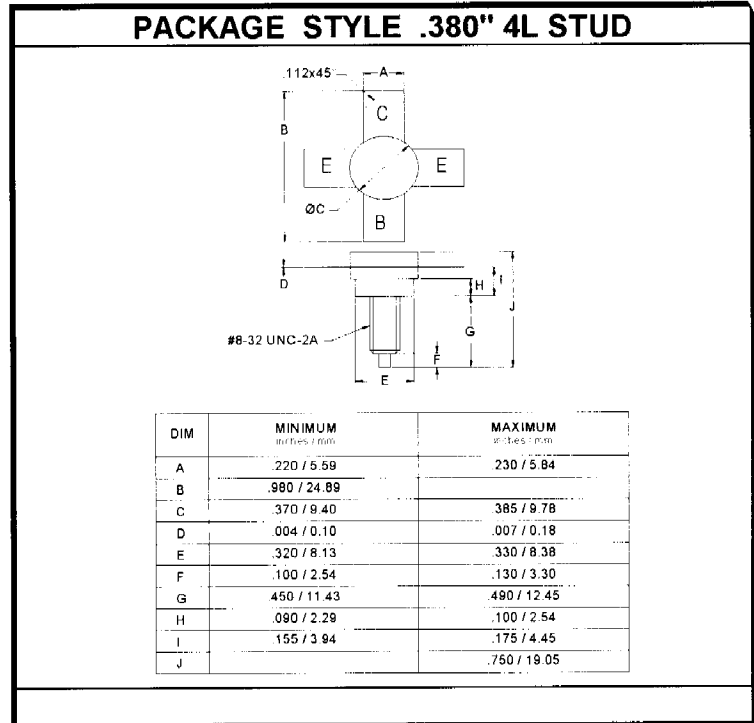
BLX13C is Designed for 28 V, Linear Amplifier, class A and AB in the HF and VHF bands.

FEATURES:

- $P_G = 21$ dB Typical at 25 W/ 28 MHz
- *Omnigold*™ Metallization System

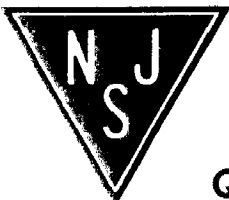
MAXIMUM RATINGS

I_C	3.0 A
V_{CE}	36 V
V_{CB}	65 V
P_{DISS}	73 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.39 °C/W



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 10$ mA	65			V
BV_{CEO}	$I_C = 50$ mA	36			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CB} = 36$ V			4.0	mA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 1.25$ A	10		100	---
C_{ob}	$V_{CB} = 28$ V $f = 1.0$ MHz		50		pF
P_G	$V_{CE} = 28$ V $P_{OUT} = 25$ W $f = 28$ MHz		21		dB
η			45		%



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